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PATENT

(b) a second atmospheric deposition station comprising an atmospheric pressure vapor deposition chamber, wherein the first atmospheric deposition station and the second atmospheric deposition station are coupled together; and

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(c) a substrate handling system adapted to transfer substrates between the first atmospheric deposition station and the second atmospheric deposition station, and wherein a plasma system is associated with the atmospheric pressure vapor deposition chamber.

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5. (Amended) The apparatus of claim 1 wherein the plasma system is a remote plasma system that is adapted to form a plasma upstream of the atmospheric pressure vapor deposition chamber.

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9. (Amended) The apparatus of claim 1 wherein the atmospheric pressure vapor deposition chamber is an atmospheric pressure chemical vapor deposition (APCVD) chamber.

11. (Amended) An apparatus for processing semiconductor substrates, the apparatus comprising:

- X4
(a) an atmospheric chemical vapor deposition chamber;
(b) a plasma system associated with the atmospheric chemical vapor deposition chamber;
(c) a spin coating chamber coupled to the atmospheric chemical vapor deposition chamber;
(d) a curing station coupled to the atmospheric chemical vapor deposition chamber; and
(e) a substrate handling system adapted to transfer substrates between the atmospheric chemical vapor deposition chamber, the spin coating chamber, and the curing station.
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